

MOSFET – N-Channel QFET

250 V, 40 A, 70 mΩ

FQA40N25

Description

This N-Channel enhancement mode power MOSFET is produced using onsemi's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

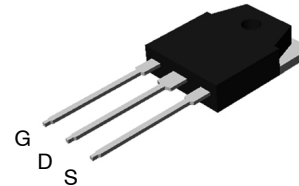
- 40 A, 250 V, $R_{DS(on)}$ = 70 mΩ (Max) @ V_{GS} = 10 V, I_D = 20 A
- Low Gate Charge (Typ. 85 nC)
- Low C_{rss} (Typ. 70 pF)
- 100% Avalanche Tested
- This is a Pb-Free Device

ABSOLUTE MAXIMUM RATINGS

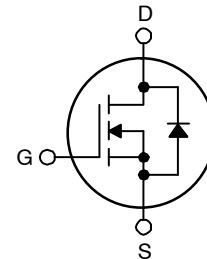
(T_C = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-Source Voltage	250	V
I_D	Drain Current Continuous (T_C = 25°C) Continuous (T_C = 100°C)	40 25	A
I_{DM}	Drain Current – Pulsed (Note 1)	160	A
V_{GSS}	Gate to Source Voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	800	mJ
I_{AR}	Avalanche Current (Note 1)	40	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	28	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P_D	Power Dissipation (T_C = 25°C) – Derate above 25°C	280 2.22	W W/°C
T_J, T_{STG}	Operating and Storage Temperature Range	–55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purposes, 1/8" from Case for 5 Seconds	300	°C

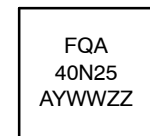
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



TO-3P-3LD / EIAJ SC-65, ISOLATED
CASE 340BZ



MARKING DIAGRAM



FQA40N25 = Specific Device Code
A = Assembly Location
YWW = Date Code (Year & Week)
ZZ = Assembly Lot

ORDERING INFORMATION

Device	Package	Shipping
FQA40N25	TO-3P (Pb-Free)	450 Unit / Tube

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max	0.45	°C/W
$R_{\theta CS}$	Thermal Resistance, Junction-to-Sink, Typ	0.24	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max	40	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTIC

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	250	–	–	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	–	0.24	–	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$	–	–	1	μA
		$V_{DS} = 200\text{ V}, T_C = 125^\circ\text{C}$	–	–	10	
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	–	–	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	–	–	-100	

ON CHARACTERISTICS

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.0	–	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$	–	0.051	0.07	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 20\text{ A}$	–	29	–	S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	–	3100	4000	pF
C_{oss}	Output Capacitance		–	620	800	pF
C_{rss}	Reverse Transfer Capacitance		–	70	90	pF

SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 125\text{ V}, I_D = 40\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4)	–	70	150	ns
t_r	Turn-On Rise Time		–	580	1150	ns
$t_{d(off)}$	Turn-Off Delay Time		–	120	250	ns
t_f	Turn-Off Fall Time		–	165	340	ns
Q_g	Total Gate Charge	$V_{DS} = 200\text{ V}, I_D = 40\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4)	–	85	110	nC
Q_{gs}	Gate-Source Charge		–	25	–	nC
Q_{gd}	Gate-Drain Charge		–	46	–	nC

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

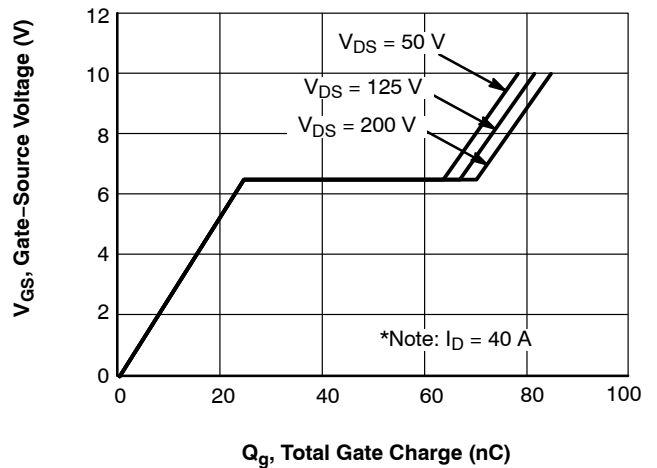
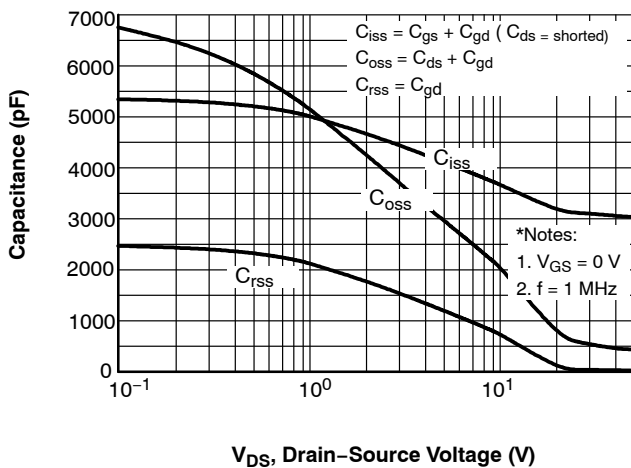
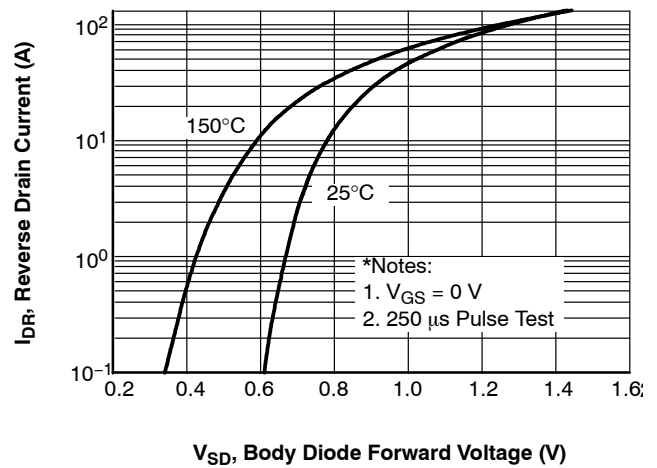
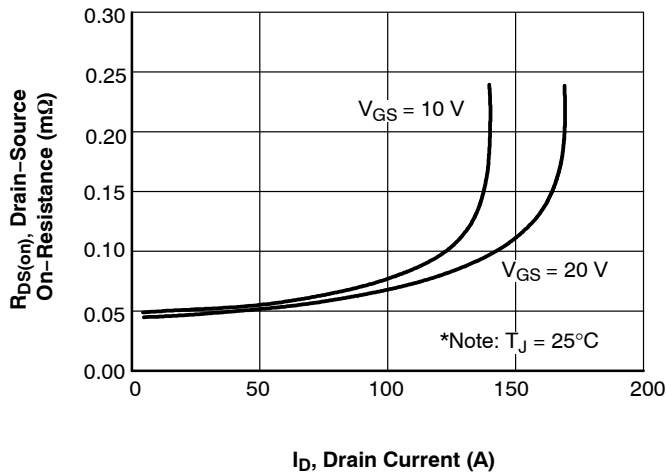
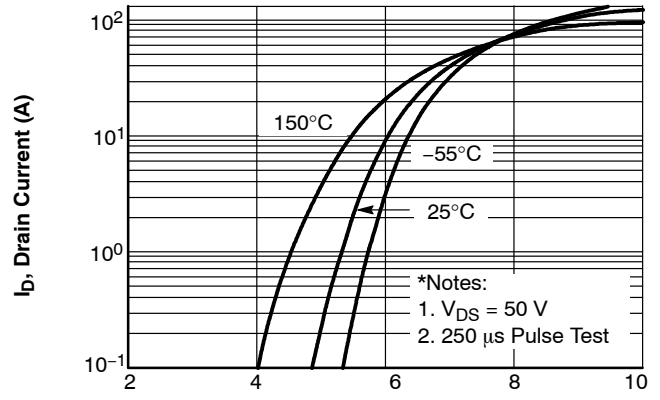
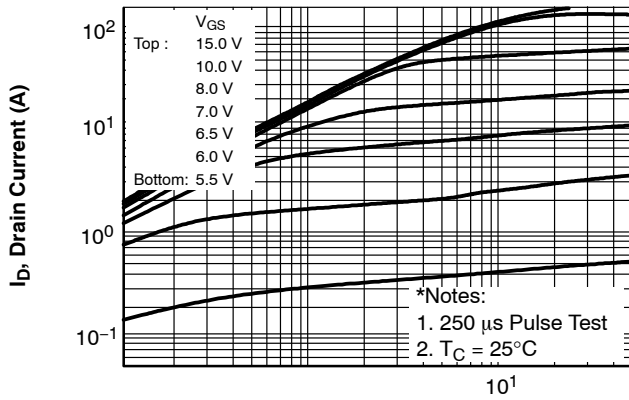
I _S	Maximum Continuous Drain–Source Diode Forward Current		–	–	40	A
I _{SM}	Maximum Pulsed Drain–Source Diode Forward Current		–	–	160	A
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 40 A	–	–	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 40 A, dI _F /dt = 100 A/μs	–	220	–	ns
Q _{rr}	Reverse Recovery Charge		–	2.0	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. $L = 0.8\text{ mH}$, $I_{AS} = 40\text{ A}$, $V_{DD} = 50\text{ V}$, $R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 40\text{ A}$, $di/dt \leq 300\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.



TYPICAL CHARACTERISTICS



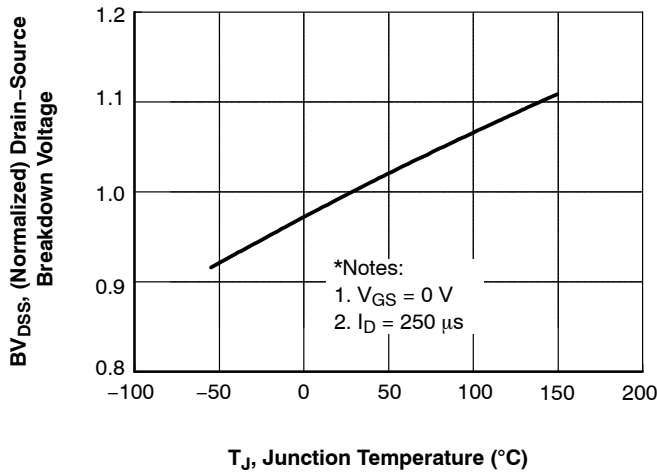
TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

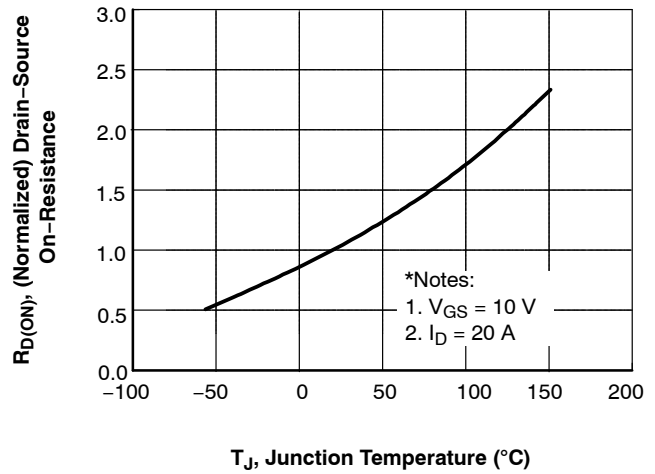


Figure 8. On-Resistance Variation vs. Temperature

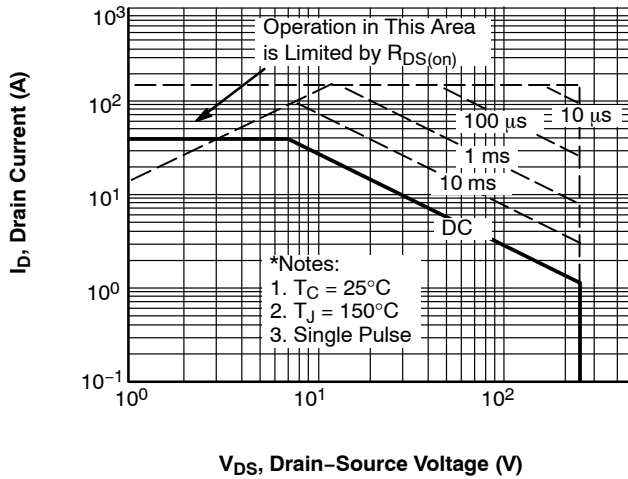


Figure 9. Maximum Safe Operating Area

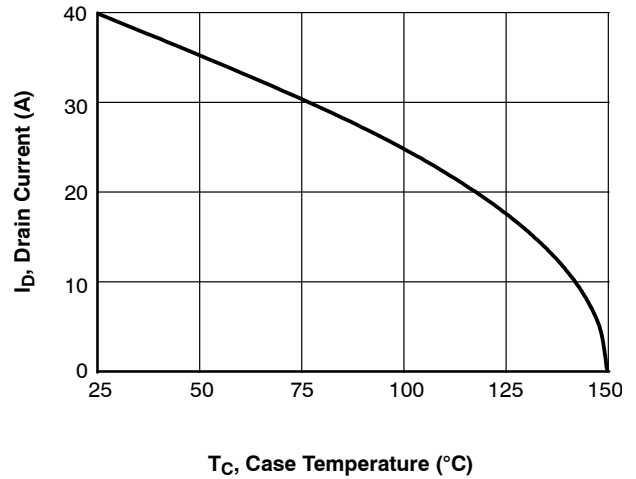


Figure 10. Maximum Drain Current vs. Case Temperature

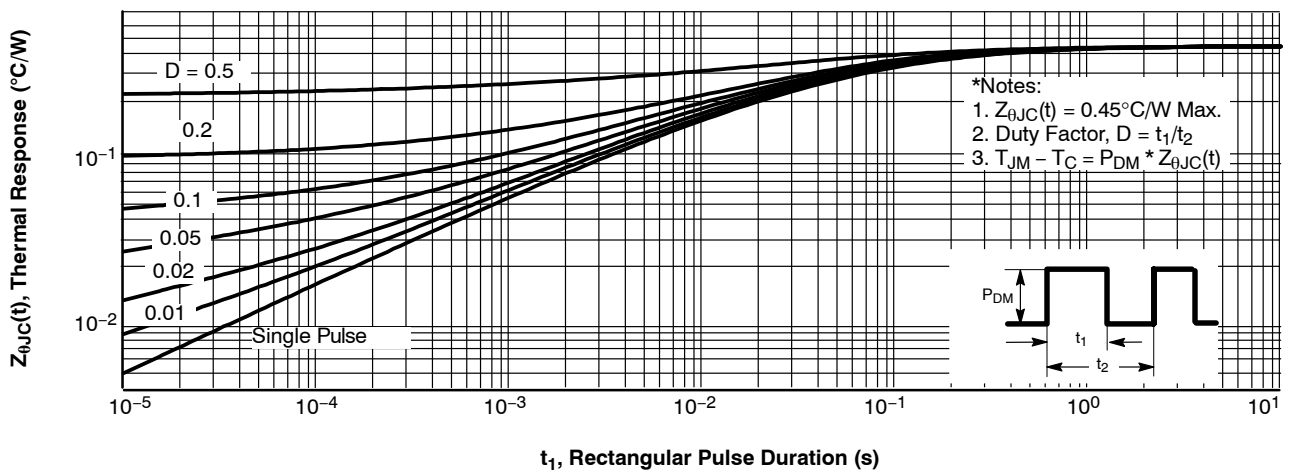


Figure 11. Transient Thermal Response Curve

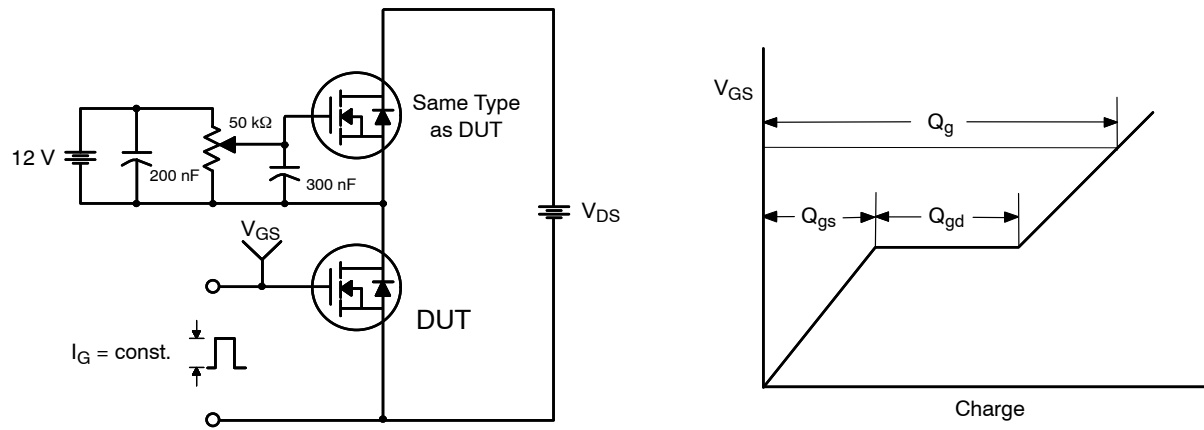


Figure 12. Gate Charge Test Circuit & Waveform

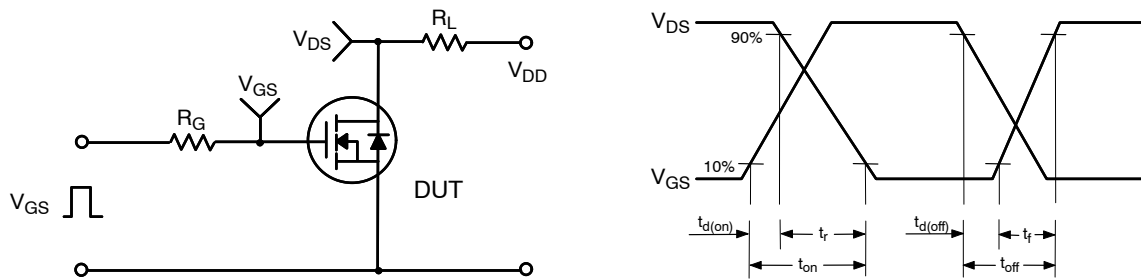


Figure 13. Resistive Switching Test Circuit & Waveforms

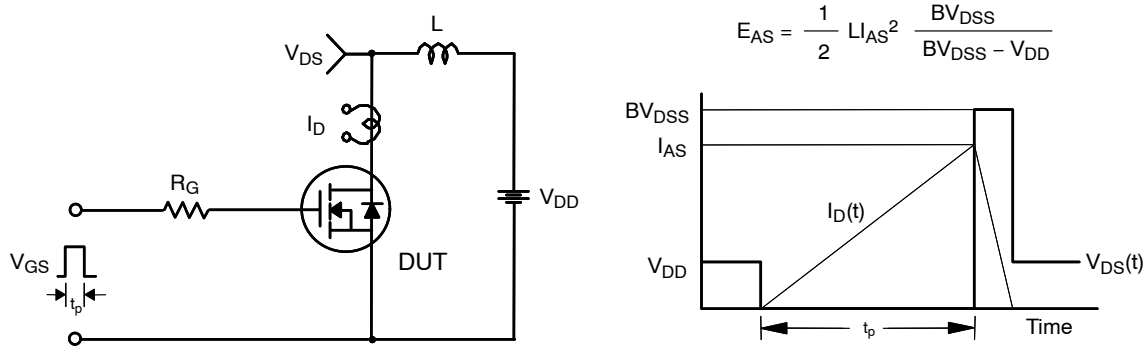


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

FQA40N25

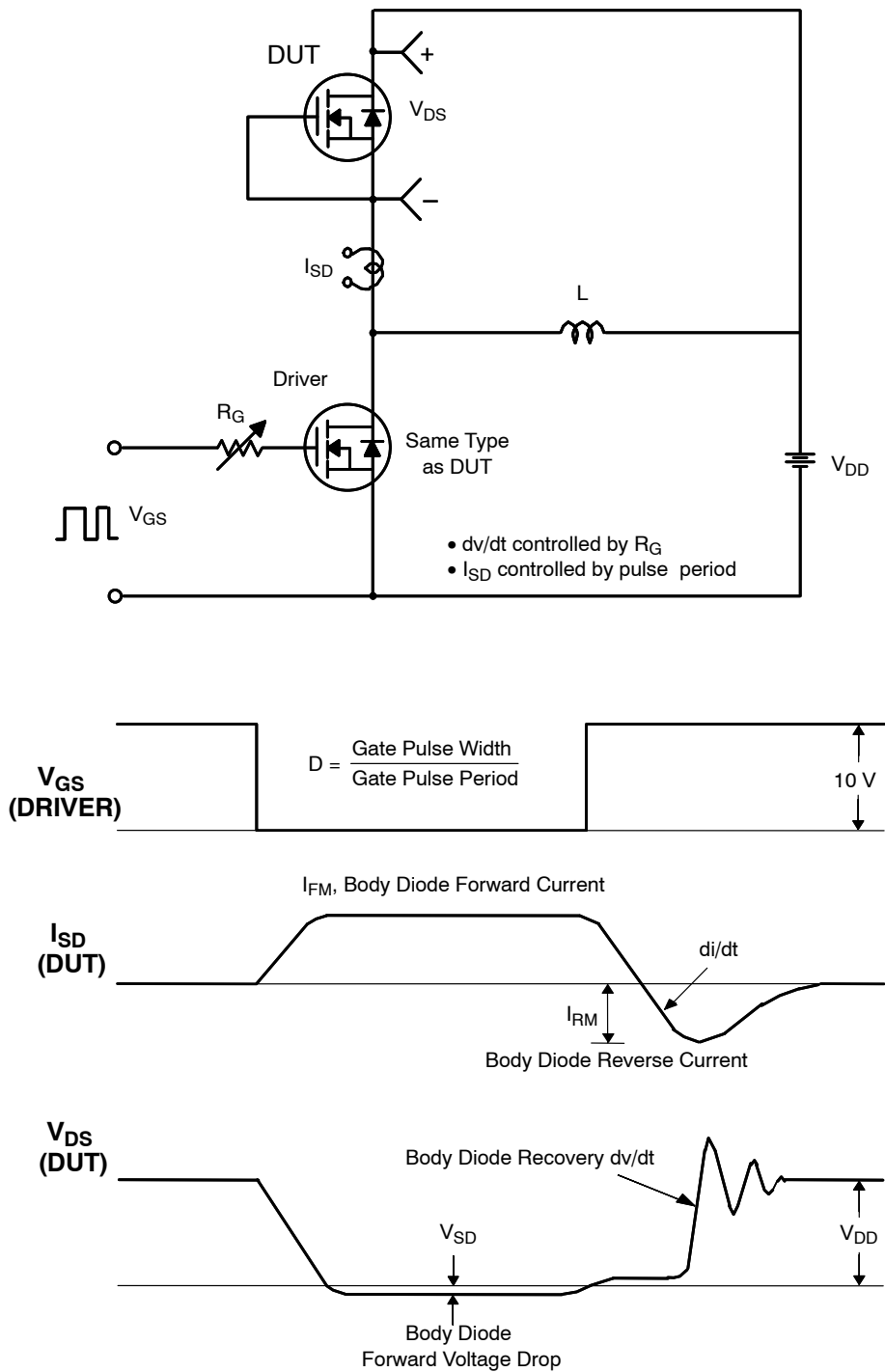
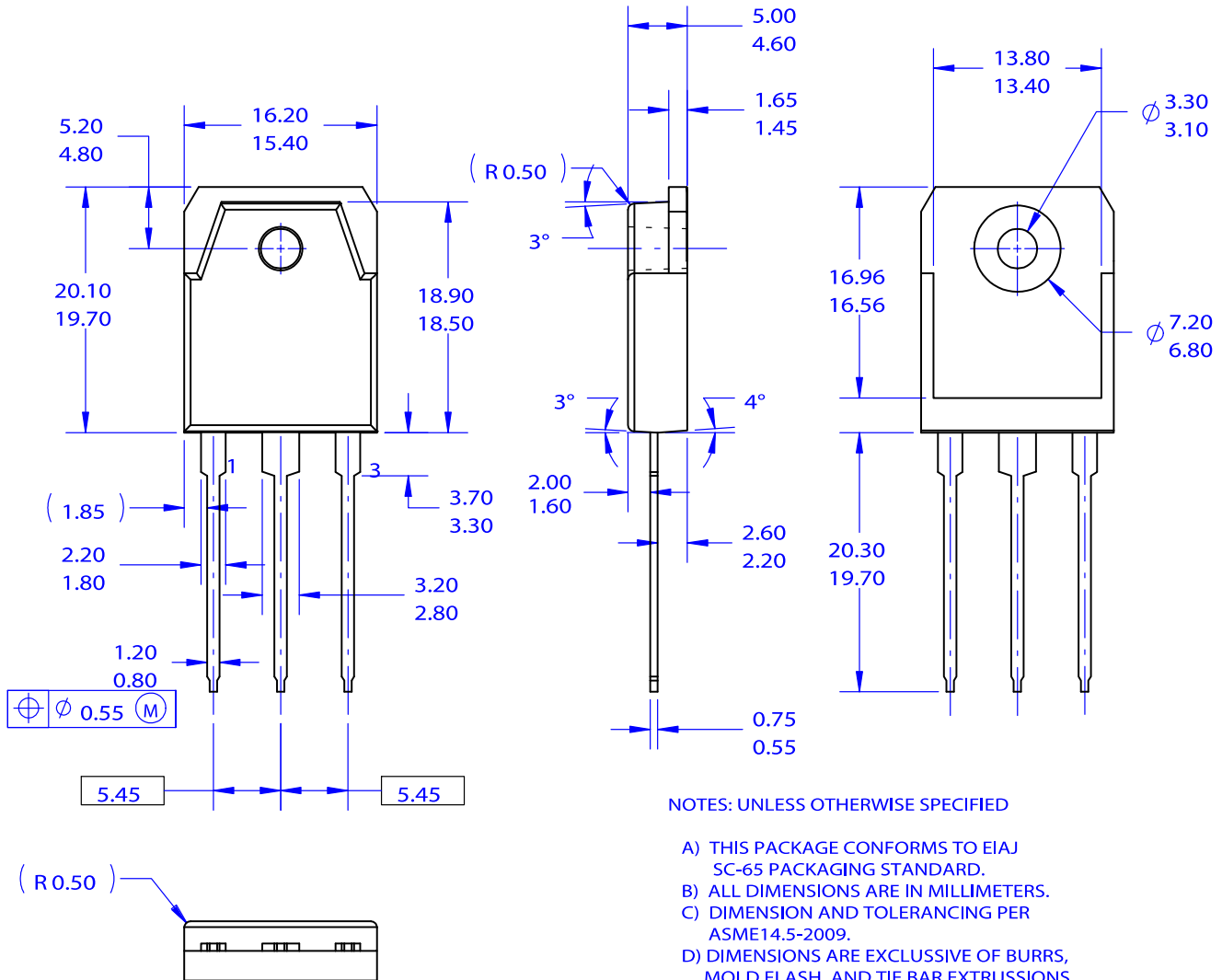


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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CASE 340BZ
ISSUE O

DATE 31 OCT 2016



NOTES: UNLESS OTHERWISE SPECIFIED

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- B) ALL DIMENSIONS ARE IN MILLIMETERS.
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